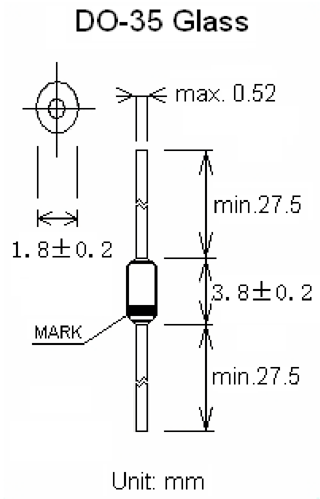


DO-35 玻封开关二极管
DO-35 Glass Switching Diode

特征 Features

- 开关速度小于 4.0nS; Fast Switching Device (TRR <4.0 nS)
- 最大功率耗散 500mW; Power Dissipation of 500mW
- 高稳定性和可靠性。High Stability and High Reliability
- 反向漏电流小。Low reverse leakage

机械数据 Mechanical Data

- 封装: DO-35 玻璃封装 Case: DO-35 Glass Case
- 极性: 色环端为负极 Polarity: Color band denotes cathode end
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25℃ 除非另有规定)
Maximum Ratings & Thermal Characteristics (Ratings at 25℃ ambient temperature unless otherwise specified.)

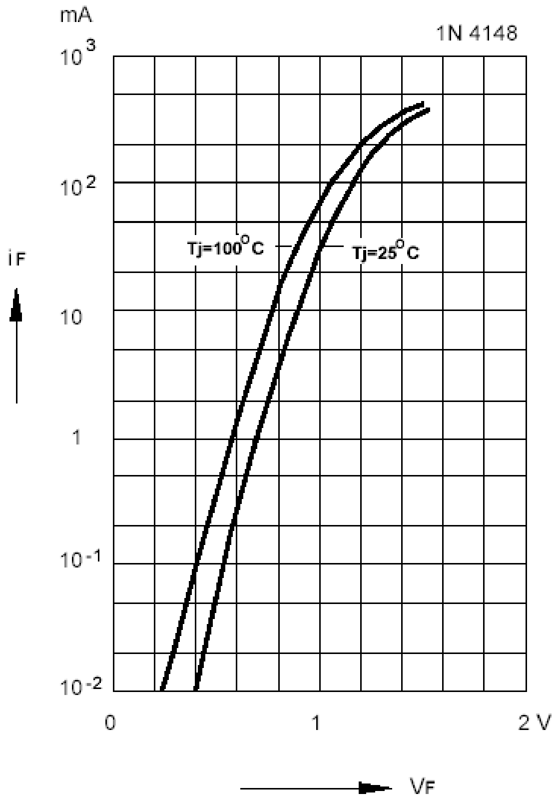
参数 Parameters	符号 Symbol	数值 Value	单位 Unit
反向电压 Reverse Voltage	V_R	75	V
反向峰值电压 Peak Reverse Voltage	V_{RM}	100	V
功率消耗 Power Dissipation	Pd	500	mW
工作结温 Operating junction temperature	Tj	175	℃
存储温度 Storage temperature range	Ts	-65-+200	℃
反向工作电压 Working Inverse Voltage	W_{IV}	75	V
平均整流电流 Average Rectified Current	I_O	150	mA
正向(不重复)电流 Non-repetitive Peak Forward Current @ t<1s and Tj=25℃	I_{FM}	450	mA

Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

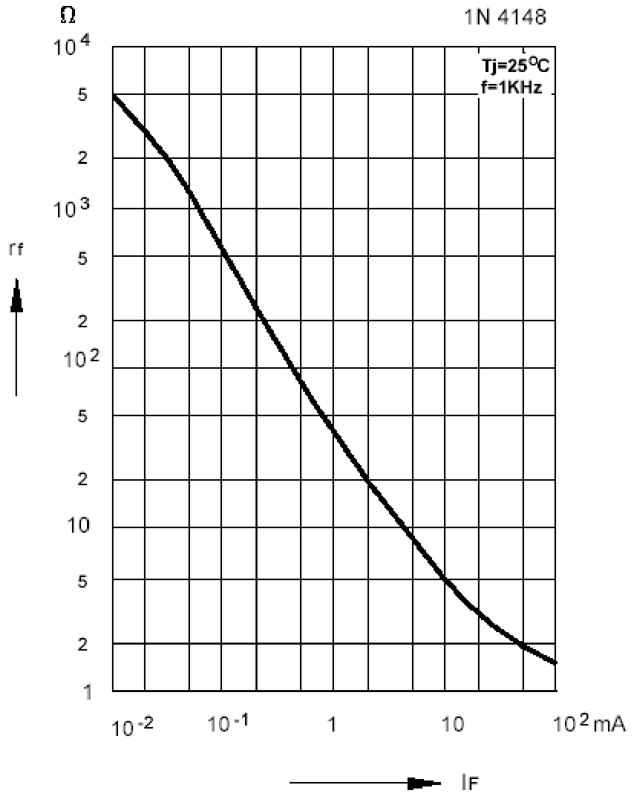
电特性 (TA = 25℃ 除非另有规定)
Electrical Characteristics (Ratings at 25℃ ambient temperature unless otherwise specified).

符号 Symbols	参数 Parameter	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
B_V	反向击穿电压 Breakdown Voltage	IR=100uA IR=5uA	100 75		V
I_R	反向漏电流 Reverse Leakage Current	VR=20V VR=75	--- ---	25 5	nA uA
V_F	正向电压 Forward Voltage 1N4448/1N914B	IF=5mA	0.62	0.72	V
	1N4148	IF=10mA	---	1	
	1N4448/1N914B	IF=100mA	---	1	
T_{RR}	反向恢复时间 Reverse Recovery Time	IF= 10mA, IR=1.0mA RL=100Ω IRR=1mA	---	4	nS
C	结电容 Capacitance	VR=0V, f=1MHZ	---	4	pF

Forward characteristics

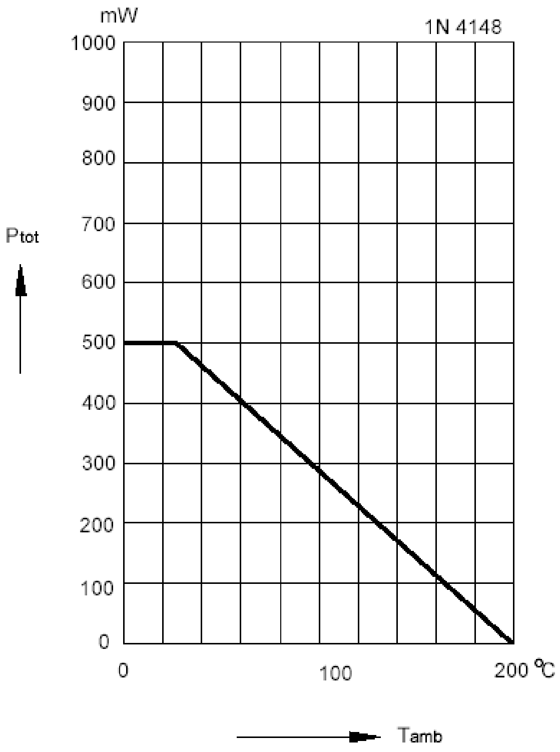


Dynamic forward resistance versus forward current

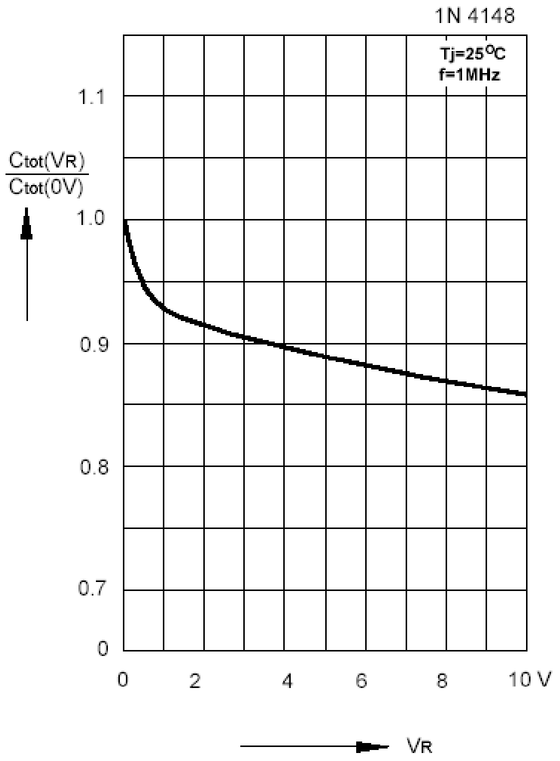


Admissible power dissipation versus ambient temperature

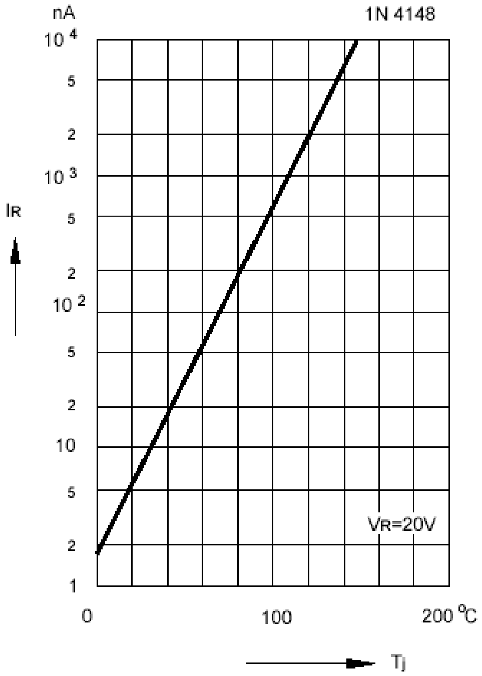
Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature



Relative capacitance versus reverse voltage



Leakage current versus junction temperature



Admissible repetitive peak forward current versus pulse duration

Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature